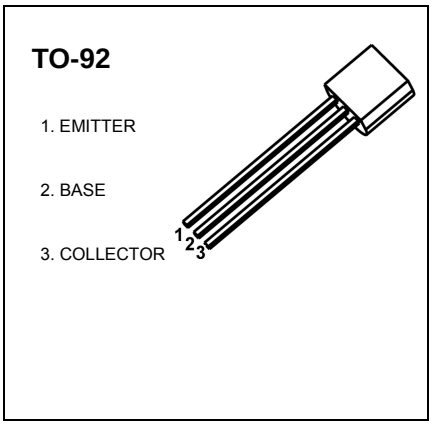
TIGER ELECTRONIC CO.,LTD

RoHS COMPLIANT

TO-92 Plastic-Encapsulate Transistors

S9014 TRANSISTOR (NPN)



FEATURES

- High Total Power Dissipation.(P_C=0.45W)
- High h_{FE} and Good Linearity
- Complementary to S9015

MAXIMUM RATINGS (T_a=25℃ unless otherwise noted)

Symbol	Parameter	Value	Unit
V_{CBO}	Collector-Base Voltage	50	V
V_{CEO}	Collector-Emitter Voltage	45	V
V_{EBO}	Emitter-Base Voltage	5	V
I_C	Collector Current -Continuous	0.1	A
P_C	Collector Power Dissipation	0.45	W
T_J	Junction Temperature	150	℃
T_{stg}	Storage Temperature	-55-150	℃

ELECTRICAL CHARACTERISTICS (T_a=25℃ unless otherwise specified)

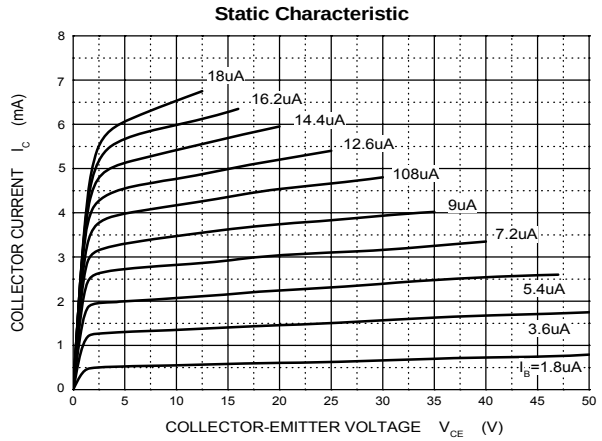
Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	$V_{(BR)CBO}$	I_C=100μA, I_E=0	50			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	I_C= 1mA, I_B=0	45			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	I_E=100μA, I_C=0	5			V
Collector cut-off current	I_{CBO}	V_{CB}=50V, I_E=0			0.1	μA
Collector cut-off current	I_{CEO}	V_{CE}=35V, I_B=0			0.1	μA
Emitter cut-off current	I_{EBO}	V_{EB}= 5V, I_C=0			0.1	μA
DC current gain	h_{FE}	V_{CE}=5V, I_C= 1mA	60		1000	
Collector-emitter saturation voltage	V_{CE}(sat)	I_C=100mA, I_B= 5mA			0.3	V
Base-emitter saturation voltage	V_{BE}(sat)	I_C=100mA, I_B= 5mA			1	V
Transition frequency	f_T	V_{CE}=5V, I_C= 10mA f=30MHz	150			MHz

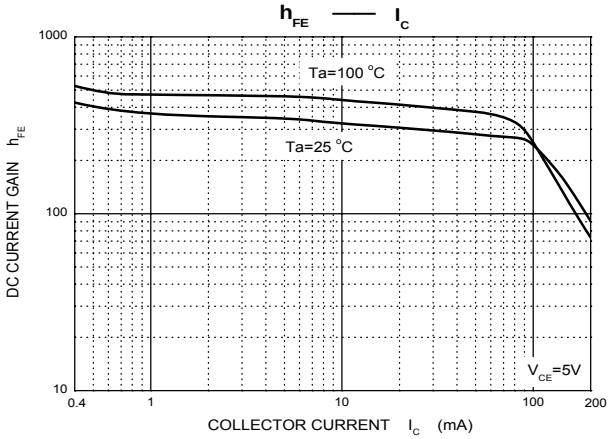
CLASSIFICATION OF $h_{FE(1)}$

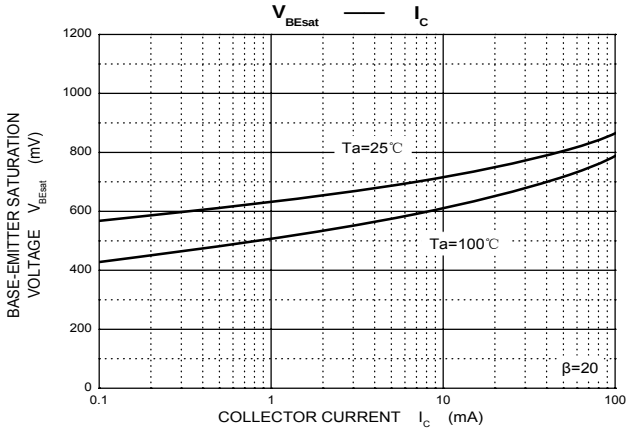
Rank	A	B	C	
Range	60-150	100-300	300-400	

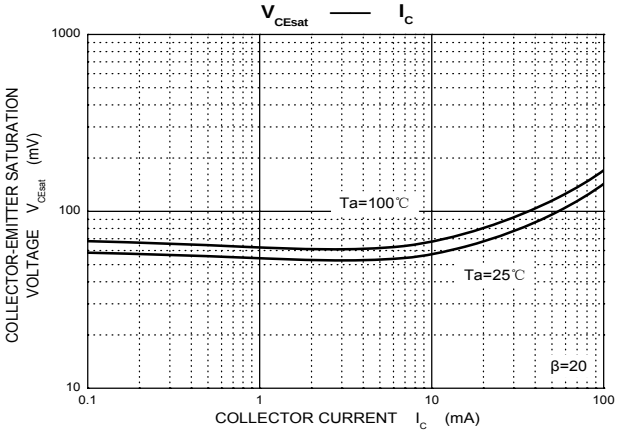
Download from alldatasheet.com

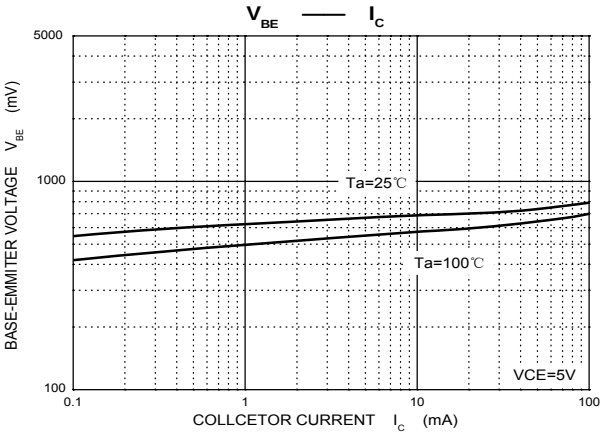
Typical Characteristics

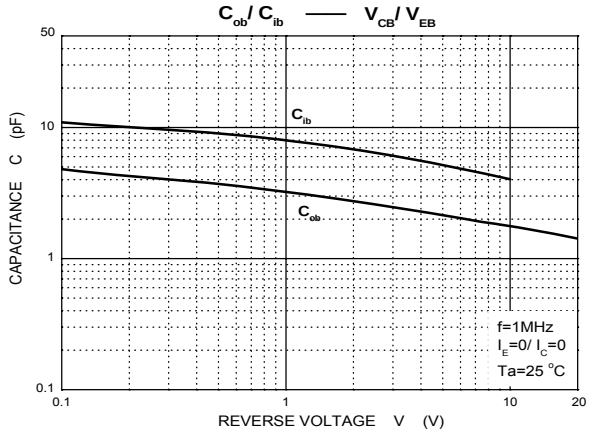


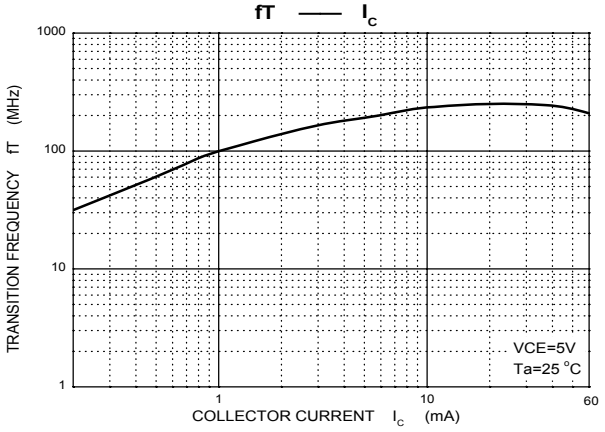


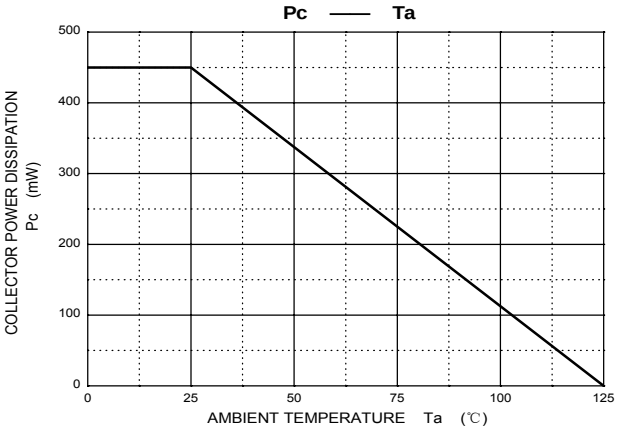












Download from alldatasheet.com